

Xiuyan Li

List of Publications by Year in descending order

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11
papers

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citations

1937685

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1872680

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all docs

11
docs citations

11
times ranked

159
citing authors

#	ARTICLE	IF	CITATIONS
1	Flexible bioelectrodes with enhanced wrinkle microstructures for reliable electrochemical modification and neuromodulation in vivo. Biosensors and Bioelectronics, 2019, 135, 181-191.	10.1	37
2	Stepwise internal potential jumps caused by multiple-domain polarization flips in metal/ferroelectric/metal/paraelectric/metal stack. Nature Communications, 2020, 11, 1895.	12.8	14
3	Effect of nitrogen passivation on interface composition and physical stress in SiO ₂ /SiC(4H) structures. Applied Physics Letters, 2018, 113, .	3.3	12
4	Direct relationship between sub-60 mV/dec subthreshold swing and internal potential instability in MOSFET externally connected to ferroelectric capacitor. , 2018, , .		9
5	Interface reaction kinetics in SiGe oxidation. Applied Physics Letters, 2019, 115, .	3.3	6
6	Analysis of Using Negative Capacitance FETs to Optimize Linearity Performance for Voltage Reference Generators. IEEE Transactions on Electron Devices, 2021, 68, 5864-5871.	3.0	3
7	Analytical Formulation of SiO ₂ -IL scavenging in HfO ₂ /SiO ₂ /Si gate stacks - A key is the SiO ₂ /Si interface reaction. , 2014, , .		2
8	The electronics transport mechanism of grain and grain boundary in semiconductive hafnium oxynitride thin film. Journal of Materials Science, 2020, 55, 2881-2890.	3.7	2
9	Kinetic model for scavenging of SiO ₂ interface layer in HfO ₂ gate stacks. , 2014, , .		1
10	On the physical origins of time-dependent steep SS in FeFET. , 2020, , .		1
11	Self-decomposition of SiO ₂ due to Si-chemical potential increase in SiO ₂ between HfO ₂ and substrate - Comprehensive understanding of SiO ₂ -IL scavenging in HfO ₂ gate stacks on Si, SiGe and SiC. , 2015, , .		0